



- Drafts
- Pending
- Active
 - L1: (1) ("6660579").PN.
 - L2: (4956) memory adj cell and NMOS
 - L3: (0) 2 and three-implant adj channel
 - L4: (0) 2 and three-implant
 - L5: (0) 2 and thre adj -implant adj chan
 - L6: (1) 2 and three adj implant adj chan
 - L7: (1) three adj implant adj channel
 - L9: (5815395) 4,924,278
 - L10: (112) "4924278"
 - L11: (51) "4924278"
 - L12: (2) ("4924278").PN.
 - L13: (2) ("5587945").PN.
 - L14: (2) ("5596524").PN.
 - L15: (2) ("5761116").PN.
 - L16: (2) ("6208559").PN.
 - L17: (2) ("6406955").PN.
 - L18: (2) ("6468849").PN.
 - L19: (2) ("6001691").PN.
 - L20: (2) ("6143594").PN.
 - L21: (2) ("6258645").PN.
 - L8: (518) implant adj channel
 - L22: (43) three adj implant
 - L23: (1) 22 and NMOS and PMOS and t
 - L24: (1) 22 and NMOS and PMOS
- Failed
- Saved

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Plurals
 Highlight all hit terms initially

Default operator: OR

22 and NMOS and PMOS

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6660579 B1	20031209	11	Zero power memory cell with improved data retention	438/217	438/276; 438/289	